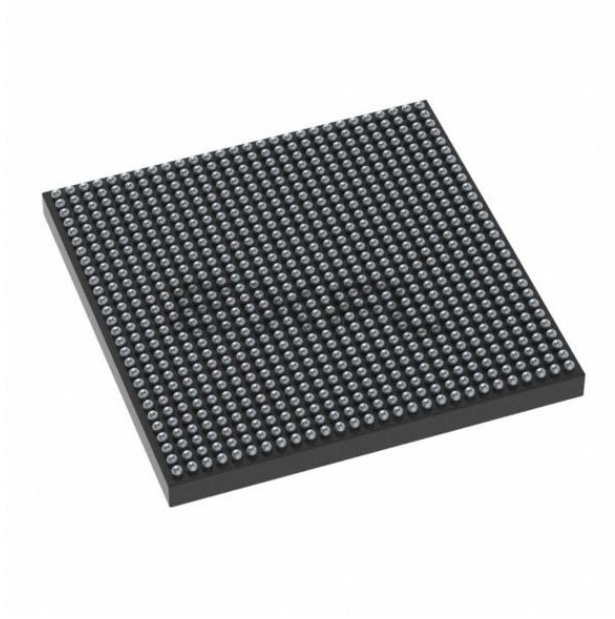

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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	Dual ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM®Cortex™-R5 with CoreSight™
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	533MHz, 1.3GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 154K+ Logic Cells
Operating Temperature	0°C ~ 100°C (TJ)
Package / Case	784-BFBGA, FCBGA
Supplier Device Package	784-FCBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu3cg-2sfvc784e

Recommended Operating Conditions

Table 2: **Recommended Operating Conditions(1)(2)**

Symbol	Description	Min	Typ	Max	Units
Processor System					
$V_{CC\_PSINTFP}$(3)	PS full-power domain supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PS full-power domain supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS full-power domain supply voltage.	0.873	0.900	0.927	V
$V_{CC\_PSINTLP}$	PS low-power domain supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PS low-power domain supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS low-power domain supply voltage.	0.873	0.900	0.927	V
V_{CC_PSAUX}	PS auxiliary supply voltage.	1.710	1.800	1.890	V
$V_{CC\_PSINTFP\_DDR}$(3)	PS DDR controller and PHY supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PS DDR controller and PHY supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS DDR controller and PHY supply voltage.	0.873	0.900	0.927	V
V_{CC_PSADC}	PS SYSMON ADC supply voltage relative to GND_PSADC.	1.710	1.800	1.890	V
V_{CC_PSPLL}	PS PLL supply voltage.	1.164	1.200	1.236	V
$V_{PS\_MGTRAVCC}$	PS-GTR supply voltage.	0.825	0.850	0.875	V
$V_{PS\_MGTRAVTT}$	PS-GTR termination voltage.	1.746	1.800	1.854	V
V_{CCO_PSDDR}(4)	PS DDR I/O supply voltage.	1.06	–	1.575	V
$V_{CC\_PSDDR\_PLL}$	PS DDR PLL supply voltage.	1.710	1.800	1.890	V
V_{CCO_PSIO}(5)	PS I/O supply.	1.710	–	3.465	V
V_{PSIN}	PS I/O input voltage.	–0.200	–	V_{CCO_PSIO} + 0.200	V
	PS DDR I/O input voltage.	–0.200	–	V_{CCO_PSDDR} + 0.200	
V_{CC_PSBATT}(6)	PS battery-backed RAM and battery-backed real-time clock (RTC) supply voltage.	1.200	–	1.500	V
Programmable Logic					
V_{CCINT}	PL internal supply voltage.	0.825	0.850	0.876	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PL internal supply voltage.	0.698	0.720	0.742	V
	For -3E devices: PL internal supply voltage.	0.873	0.900	0.927	V
V_{CCINT_IO}(7)	PL internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PL internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -3E devices: PL internal supply voltage for the I/O banks.	0.873	0.900	0.927	V
V_{CCBRAM}	Block RAM supply voltage.	0.825	0.850	0.876	V
	For -3E devices: block RAM supply voltage.	0.873	0.900	0.927	V
V_{CCAUX}	Auxiliary supply voltage.	1.746	1.800	1.854	V

Table 4: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ(1)	Max	Units
I_{CC_PSBATT}(4)(5)	Battery supply current at V_{CC_PSBATT} = 1.50V, RTC enabled.	–	–	3650	nA
	Battery supply current at V_{CC_PSBATT} = 1.50V, RTC disabled.	–	–	650	nA
	Battery supply current at V_{CC_PSBATT} = 1.20V, RTC enabled.	–	–	3150	nA
	Battery supply current at V_{CC_PSBATT} = 1.20V, RTC disabled.	–	–	150	nA
I_{PSFS}(6)	PS V_{CC_PSAUX} additional supply current during eFUSE programming.	–	–	115	mA
Calibrated programmable on-die termination (DCI) in HP I/O banks(8) (measured per JEDEC specification)					
R(9)	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_40.	–10%(7)	40	+10%(7)	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_48.	–10%(7)	48	+10%(7)	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_60.	–10%(7)	60	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–10%(7)	40	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–10%(7)	48	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–10%(7)	60	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–10%(7)	120	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–10%(7)	240	+10%(7)	Ω
Uncalibrated programmable on-die termination in HP I/Os banks (measured per JEDEC specification)					
R(9)	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_40.	–50%	40	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_48.	–50%	48	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–50%	40	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–50%	48	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–50%	120	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–50%	240	+50%	Ω
Uncalibrated programmable on-die termination in HD I/O banks (measured per JEDEC specification)					
R(9)	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_48.	–50%	48	+50%	Ω
Internal V_{REF}	50% V_{CCO}	V_{CCO} x 0.49	V_{CCO} x 0.50	V_{CCO} x 0.51	V
	70% V_{CCO}	V_{CCO} x 0.69	V_{CCO} x 0.70	V_{CCO} x 0.71	V

Table 8: **V_{PSIN} Maximum Allowed AC Voltage Overshoot and Undershoot for PS I/O Banks(1)**

AC Voltage Overshoot	% of UI at –40°C to 100°C	AC Voltage Undershoot	% of UI at –40°C to 100°C
V_{CCO_PSIO} + 0.30	100%	–0.30	100%
V_{CCO_PSIO} + 0.35	100%	–0.35	75%
V_{CCO_PSIO} + 0.40	100%	–0.40	45%
V_{CCO_PSIO} + 0.45	100%	–0.45	40%
V_{CCO_PSIO} + 0.50	75%	–0.50	10%
V_{CCO_PSIO} + 0.55	75%	–0.55	6%
V_{CCO_PSIO} + 0.60	60%	–0.60	2%
V_{CCO_PSIO} + 0.65	30%	–0.65	0%
V_{CCO_PSIO} + 0.70	20%	–0.70	0%
V_{CCO_PSIO} + 0.75	10%	–0.75	0%
V_{CCO_PSIO} + 0.80	10%	–0.80	0%
V_{CCO_PSIO} + 0.85	8%	–0.85	0%
V_{CCO_PSIO} + 0.90	6%	–0.90	0%
V_{CCO_PSIO} + 0.95	6%	–0.95	0%

Notes:

1. A total of 200 mA per bank should not be exceeded.

Processor System (PS) Performance Characteristics

Table 28: **Processor Performance**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
F_{APUMAX}	Maximum APU clock frequency.	1500	1333	1200	MHz
F_{RPUMAX}	Maximum RPU clock frequency.	600	533	500	MHz
F_{GPUMAX}	Maximum GPU clock frequency.	667	600	600	MHz

Table 29: **Configuration and Security Unit Performance**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
$F_{CSUCIBMAX}$	Maximum CSU crypto interface block frequency.	400	400	400	MHz

Table 30: **PS DDR Performance**

Memory Standard	Package	DRAM Type	Speed Grade						Units
			-3		-2		-1		
			Min	Max	Min	Max	Min	Max	
DDR4	All FFV packages, FBVB900, and SFVC784	Single rank component	664	2400	664	2400	664	2400	Mb/s
		1 rank DIMM(1)(2)	664	2133	664	2133	664	2133	Mb/s
		2 rank DIMM(1)(3)	664	1866	664	1866	664	1866	Mb/s
	SFVA625	Single rank component	664	2133	664	2133	664	2133	Mb/s
		1 rank DIMM(1)(2)	664	1866	664	1866	664	1866	Mb/s
		2 rank DIMM(1)(3)	664	1600	664	1600	664	1600	Mb/s
	SBVA484	Single rank component	664	1066	664	1066	664	1066	Mb/s
		1 rank DIMM(1)(2)	664	1066	664	1066	664	1066	Mb/s
		2 rank DIMM(1)(3)	664	1066	664	1066	664	1066	Mb/s
LPDDR4	All FFV packages, FBVB900 and SFVC784	Single die package(5)	664	2400	664	2400	664	2400	Mb/s
		Dual die package(4)(5)	664	2133	664	2133	664	2133	Mb/s
	SFVA625	Single die package(5)	664	2133	664	2133	664	2133	Mb/s
		Dual die package(4)(5)	664	1866	664	1866	664	1866	Mb/s
	SBVA484	Single die package(5)	664	1066	664	1066	664	1066	Mb/s
		Dual die package(4)(5)	664	1066	664	1066	664	1066	Mb/s

Table 67: **USB 3.0 Protocol Characteristics (PS-GTR Transceivers)**

Standard	Description	Line Rate (Mb/s)	Min	Max	Units
USB 3.0 Transmitter Jitter Generation					
USB 3.0	Total transmitter jitter.	5000	–	0.66	UI
USB 3.0 Receiver High Frequency Jitter Tolerance					
USB 3.0	Total receiver jitter tolerance.	5000	0.2	–	UI

Table 68: **Serial-GMII Protocol Characteristics (PS-GTR Transceivers)**

Standard	Description	Line Rate (Mb/s)	Min	Max	Units
Serial-GMII Transmitter Jitter Generation					
SGMII	Deterministic transmitter jitter.	1250	–	0.25	UI
Serial-GMII Receiver High Frequency Jitter Tolerance					
SGMII	Total receiver jitter tolerance.	1250	0.25	–	UI

PS System Monitor Specifications

Table 69: **PS SYSMON Specifications**

Parameter	Comments	Conditions	Min	Typ	Max	Units
V_{CC_PSADC} = 1.8V ±3%, T_j = –40°C to 100°C, typical values at T_j = 40°C						
ADC Accuracy (T_j = –55°C to 125°C) (1)						
Resolution			10	–	–	Bits
Sample rate			–	–	1	MS/s
RMS code noise	On-chip reference		–	1	–	LSBs
On-Chip Sensor Accuracy						
Temperature sensor error		T_j = –55°C to 110°C	–	–	±3.5	°C
		T_j = 110°C to 125°C	–	–	±5	°C
Supply sensor error(2)	Supply voltages less than or electrically connected to V_{CC_PSADC}.	T_j = –40°C to 125°C	–	–	±1	%
	Supply voltages nominally at 1.8V but with the potential to go above V_{CC_PSADC}.	T_j = –40°C to 125°C	–	–	±1.5	%
	Supply voltages nominally in the 2.0V to 3.3V range.	T_j = –40°C to 125°C	–	–	±2.5	%

Notes:

1. ADC offset errors are removed by enabling the ADC automatic offset calibration feature. The values are specified for when this feature is enabled.
2. Supply sensor offset and gain errors are removed by enabling the automatic offset and gain calibration feature. The values are specified for when this feature is enabled.

Table 72: **MIPI D-PHY Performance**

Description	I/O Bank Type	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3[1]	-2[1]	-1	-2	-1	
MIPI D-PHY transmitter or receiver.	HP	1500	1500	1260	1260	1260	Mb/s

Notes:
1. In the SBVA484 package, the data rate is 1260 Mb/s.

Table 73: **LVDS Native-Mode 1000BASE-X Support[1]**

Description	I/O Bank Type	Speed Grade and V_{CCINT} Operating Voltages				
		0.90V	0.85V		0.72V	
		-3	-2	-1	-2	-1
1000BASE-X	HP	Yes				

Notes:
1. 1000BASE-X support is based on the *IEEE Standard for CSMA/CD Access Method and Physical Layer Specifications* (IEEE Std 802.3-2008).

Table 74 provides the maximum data rates for applicable memory standards using the Zynq UltraScale+ MPSoC memory PHY. Refer to Memory Interfaces for the complete list of memory interface standards supported and detailed specifications. The final performance of the memory interface is determined through a complete design implemented in the Vivado Design Suite, following guidelines in the *UltraScale Architecture PCB Design Guide* (UG583), electrical analysis, and characterization of the system.

Table 74: **Maximum Physical Interface (PHY) Rate for Memory Interfaces**

Memory Standard	Package[1]	DRAM Type	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
DDR4	All FFV packages and FBVB900	Single rank component	2666	2666	2400	2400	2133	Mb/s
		1 rank DIMM[2][3][4]	2400	2400	2133	2133	1866	Mb/s
		2 rank DIMM[2][5]	2133	2133	1866	1866	1600	Mb/s
		4 rank DIMM[2][6]	1600	1600	1333	1333	N/A	Mb/s
	SFVC784	Single rank component	2400	2400	2133	2133	1866	Mb/s
		1 rank DIMM[2][3]	2133	2133	1866	1866	1600	Mb/s
		2 rank DIMM[2][5]	1866	1866	1600	1600	1600	Mb/s
DDR3	All FFV packages and FBVB900	Single rank component	2133	2133	2133	2133	1866	Mb/s
		1 rank DIMM[2][3]	1866	1866	1866	1866	1600	Mb/s
		2 rank DIMM[2][5]	1600	1600	1600	1600	1333	Mb/s
		4 rank DIMM[2][6]	1066	1066	1066	1066	800	Mb/s
	SFVC784	Single rank component	1866	1866	1866	1866	1600	Mb/s
		1 rank DIMM[2][3]	1600	1600	1600	1600	1600	Mb/s
		2 rank DIMM[2][5]	1600	1600	1600	1600	1333	Mb/s
		4 rank DIMM[2][6]	1066	1066	1066	1066	800	Mb/s

Table 75: **IOB High Density (HD) Switching Characteristics *(Cont'd)***

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
LVCMOS33_S_8	1.154	1.154	1.213	1.154	1.213	2.929	2.929	3.260	2.929	3.260	2.260	2.260	2.532	2.260	2.532	ns
LVDS_25	1.003	1.003	1.116	1.003	1.116	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
LVPECL	1.003	1.003	1.116	1.003	1.116	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
LVTTL_F_12	1.164	1.164	1.223	1.164	1.223	2.415	2.415	2.651	2.415	2.651	1.754	1.754	1.915	1.754	1.915	ns
LVTTL_F_16	1.164	1.164	1.223	1.164	1.223	2.464	2.464	2.732	2.464	2.732	1.750	1.750	1.986	1.750	1.986	ns
LVTTL_F_4	1.164	1.164	1.223	1.164	1.223	2.541	2.541	2.765	2.541	2.765	1.932	1.932	2.135	1.932	2.135	ns
LVTTL_F_8	1.164	1.164	1.223	1.164	1.223	2.582	2.582	2.787	2.582	2.787	1.910	1.910	2.063	1.910	2.063	ns
LVTTL_S_12	1.164	1.164	1.223	1.164	1.223	2.731	2.731	3.075	2.731	3.075	2.072	2.072	2.343	2.072	2.343	ns
LVTTL_S_16	1.164	1.164	1.223	1.164	1.223	2.714	2.714	3.024	2.714	3.024	2.028	2.028	2.232	2.028	2.232	ns
LVTTL_S_4	1.164	1.164	1.223	1.164	1.223	2.999	2.999	3.340	2.999	3.340	2.320	2.320	2.610	2.320	2.610	ns
LVTTL_S_8	1.164	1.164	1.223	1.164	1.223	2.929	2.929	3.260	2.929	3.260	2.260	2.260	2.532	2.260	2.532	ns
SLVS_400_25	1.020	1.020	1.136	1.020	1.136	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
SSTL12_F	0.780	0.780	0.867	0.780	0.867	1.643	1.643	1.792	1.643	1.792	1.285	1.285	1.423	1.285	1.423	ns
SSTL12_S	0.780	0.780	0.867	0.780	0.867	1.784	1.784	1.948	1.784	1.948	1.567	1.567	1.706	1.567	1.706	ns
SSTL135_F	0.798	0.798	0.881	0.798	0.881	1.625	1.625	1.765	1.625	1.765	1.341	1.341	1.458	1.341	1.458	ns
SSTL135_II_F	0.798	0.798	0.881	0.798	0.881	1.623	1.623	1.770	1.623	1.770	1.325	1.325	1.470	1.325	1.470	ns
SSTL135_II_S	0.798	0.798	0.881	0.798	0.881	1.768	1.768	1.916	1.768	1.916	1.722	1.722	1.911	1.722	1.911	ns
SSTL135_S	0.798	0.798	0.881	0.798	0.881	1.869	1.869	2.025	1.869	2.025	1.814	1.814	1.976	1.814	1.976	ns
SSTL15_F	0.838	0.838	0.880	0.838	0.880	1.612	1.612	1.754	1.612	1.754	1.357	1.357	1.464	1.357	1.464	ns
SSTL15_II_F	0.838	0.838	0.880	0.838	0.880	1.622	1.622	1.778	1.622	1.778	1.356	1.356	1.442	1.356	1.442	ns
SSTL15_II_S	0.838	0.838	0.880	0.838	0.880	1.821	1.821	1.987	1.821	1.987	1.895	1.895	2.047	1.895	2.047	ns
SSTL15_S	0.838	0.838	0.880	0.838	0.880	1.824	1.824	1.977	1.824	1.977	1.743	1.743	1.907	1.743	1.907	ns
SSTL18_II_F	0.947	0.947	1.021	0.947	1.021	1.729	1.729	1.880	1.729	1.880	1.377	1.377	1.492	1.377	1.492	ns
SSTL18_II_S	0.947	0.947	1.021	0.947	1.021	1.796	1.796	1.965	1.796	1.965	1.616	1.616	1.800	1.616	1.800	ns
SSTL18_I_F	0.947	0.947	1.021	0.947	1.021	1.609	1.609	1.755	1.609	1.755	1.220	1.220	1.313	1.220	1.313	ns
SSTL18_I_S	0.947	0.947	1.021	0.947	1.021	1.786	1.786	1.942	1.786	1.942	1.677	1.677	1.836	1.677	1.836	ns
SUB_LVDS	1.002	1.002	1.036	1.002	1.036	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns

Table 76: **IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
HSTL_I_DCI_S	0.393	0.393	0.415	0.393	0.415	0.766	0.766	0.821	0.766	0.821	0.847	0.847	0.912	0.847	0.912	ns
HSTL_I_F	0.378	0.378	0.399	0.378	0.399	0.423	0.423	0.443	0.423	0.443	0.549	0.549	0.581	0.549	0.581	ns
HSTL_I_M	0.378	0.378	0.399	0.378	0.399	0.554	0.554	0.585	0.554	0.585	0.640	0.640	0.677	0.640	0.677	ns
HSTL_I_S	0.378	0.378	0.399	0.378	0.399	0.766	0.766	0.816	0.766	0.816	0.811	0.811	0.866	0.811	0.866	ns
HSUL_12_DCI_F	0.378	0.378	0.399	0.378	0.399	0.425	0.425	0.443	0.425	0.443	0.558	0.558	0.586	0.558	0.586	ns
HSUL_12_DCI_M	0.378	0.378	0.399	0.378	0.399	0.556	0.556	0.586	0.556	0.586	0.654	0.654	0.694	0.654	0.694	ns
HSUL_12_DCI_S	0.378	0.378	0.399	0.378	0.399	0.736	0.736	0.784	0.736	0.784	0.821	0.821	0.886	0.821	0.886	ns
HSUL_12_F	0.378	0.378	0.399	0.378	0.399	0.412	0.412	0.430	0.412	0.430	0.538	0.538	0.566	0.538	0.566	ns
HSUL_12_M	0.378	0.378	0.399	0.378	0.399	0.551	0.551	0.582	0.551	0.582	0.642	0.642	0.679	0.642	0.679	ns
HSUL_12_S	0.378	0.378	0.399	0.378	0.399	0.750	0.750	0.799	0.750	0.799	0.813	0.813	0.868	0.813	0.868	ns
LVCMOS12_F_2	0.512	0.512	0.555	0.512	0.555	0.672	0.672	0.692	0.672	0.692	0.898	0.898	0.922	0.898	0.922	ns
LVCMOS12_F_4	0.512	0.512	0.555	0.512	0.555	0.504	0.504	0.521	0.504	0.521	0.664	0.664	0.693	0.664	0.693	ns
LVCMOS12_F_6	0.512	0.512	0.555	0.512	0.555	0.485	0.485	0.507	0.485	0.507	0.634	0.634	0.669	0.634	0.669	ns
LVCMOS12_F_8	0.512	0.512	0.555	0.512	0.555	0.465	0.465	0.489	0.465	0.489	0.611	0.611	0.666	0.611	0.666	ns
LVCMOS12_M_2	0.512	0.512	0.555	0.512	0.555	0.708	0.708	0.727	0.708	0.727	0.916	0.916	0.945	0.916	0.945	ns
LVCMOS12_M_4	0.512	0.512	0.555	0.512	0.555	0.550	0.550	0.573	0.550	0.573	0.664	0.664	0.690	0.664	0.690	ns
LVCMOS12_M_6	0.512	0.512	0.555	0.512	0.555	0.527	0.527	0.554	0.527	0.554	0.622	0.622	0.652	0.622	0.652	ns
LVCMOS12_M_8	0.512	0.512	0.555	0.512	0.555	0.540	0.540	0.571	0.540	0.571	0.614	0.614	0.649	0.614	0.649	ns
LVCMOS12_S_2	0.512	0.512	0.555	0.512	0.555	0.767	0.767	0.803	0.767	0.803	0.990	0.990	1.024	0.990	1.024	ns
LVCMOS12_S_4	0.512	0.512	0.555	0.512	0.555	0.666	0.666	0.704	0.666	0.704	0.803	0.803	0.848	0.803	0.848	ns
LVCMOS12_S_6	0.512	0.512	0.555	0.512	0.555	0.657	0.657	0.695	0.657	0.695	0.732	0.732	0.774	0.732	0.774	ns
LVCMOS12_S_8	0.512	0.512	0.555	0.512	0.555	0.708	0.708	0.761	0.708	0.761	0.745	0.745	0.790	0.745	0.790	ns
LVCMOS15_F_12	0.414	0.414	0.445	0.414	0.445	0.500	0.500	0.522	0.500	0.522	0.647	0.647	0.682	0.647	0.682	ns
LVCMOS15_F_2	0.414	0.414	0.445	0.414	0.445	0.702	0.702	0.722	0.702	0.722	0.919	0.919	0.940	0.919	0.940	ns
LVCMOS15_F_4	0.414	0.414	0.445	0.414	0.445	0.579	0.579	0.601	0.579	0.601	0.755	0.755	0.781	0.755	0.781	ns
LVCMOS15_F_6	0.414	0.414	0.445	0.414	0.445	0.547	0.547	0.569	0.547	0.569	0.711	0.711	0.742	0.711	0.742	ns
LVCMOS15_F_8	0.414	0.414	0.445	0.414	0.445	0.518	0.518	0.538	0.518	0.538	0.686	0.686	0.703	0.686	0.703	ns
LVCMOS15_M_12	0.414	0.414	0.445	0.414	0.445	0.607	0.607	0.644	0.607	0.644	0.637	0.637	0.676	0.637	0.676	ns
LVCMOS15_M_2	0.414	0.414	0.445	0.414	0.445	0.741	0.741	0.770	0.741	0.770	0.938	0.938	0.962	0.938	0.962	ns
LVCMOS15_M_4	0.414	0.414	0.445	0.414	0.445	0.625	0.625	0.651	0.625	0.651	0.754	0.754	0.786	0.754	0.786	ns
LVCMOS15_M_6	0.414	0.414	0.445	0.414	0.445	0.576	0.576	0.604	0.576	0.604	0.674	0.674	0.710	0.674	0.710	ns
LVCMOS15_M_8	0.414	0.414	0.445	0.414	0.445	0.568	0.568	0.601	0.568	0.601	0.639	0.639	0.681	0.639	0.681	ns
LVCMOS15_S_12	0.414	0.414	0.445	0.414	0.445	0.788	0.788	0.855	0.788	0.855	0.695	0.695	0.733	0.695	0.733	ns
LVCMOS15_S_2	0.414	0.414	0.445	0.414	0.445	0.829	0.829	0.864	0.829	0.864	1.039	1.039	1.079	1.039	1.079	ns
LVCMOS15_S_4	0.414	0.414	0.445	0.414	0.445	0.687	0.687	0.725	0.687	0.725	0.813	0.813	0.851	0.813	0.851	ns
LVCMOS15_S_6	0.414	0.414	0.445	0.414	0.445	0.671	0.671	0.710	0.671	0.710	0.726	0.726	0.763	0.726	0.763	ns
LVCMOS15_S_8	0.414	0.414	0.445	0.414	0.445	0.704	0.704	0.755	0.704	0.755	0.721	0.721	0.758	0.721	0.758	ns
LVCMOS18_F_12	0.418	0.418	0.445	0.418	0.445	0.573	0.573	0.601	0.573	0.601	0.731	0.731	0.769	0.731	0.769	ns
LVCMOS18_F_2	0.418	0.418	0.445	0.418	0.445	0.739	0.739	0.760	0.739	0.760	0.945	0.945	0.971	0.945	0.971	ns
LVCMOS18_F_4	0.418	0.418	0.445	0.418	0.445	0.609	0.609	0.630	0.609	0.630	0.778	0.778	0.802	0.778	0.802	ns
LVCMOS18_F_6	0.418	0.418	0.445	0.418	0.445	0.603	0.603	0.633	0.603	0.633	0.781	0.781	0.808	0.781	0.808	ns

DSP48 Slice Switching Characteristics

Table 83: **DSP48 Slice Switching Characteristics**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
Maximum Frequency							
F_{MAX}	With all registers used.	891	775	645	644	600	MHz
F_{MAX_PATDET}	With pattern detector.	794	687	571	562	524	MHz
$F_{MAX\_MULT\_NOMREG}$	Two register multiply without MREG.	635	544	456	440	413	MHz
$F_{MAX\_MULT\_NOMREG\_PATDET}$	Two register multiply without MREG with pattern detect.	577	492	410	395	371	MHz
$F_{MAX\_PREADD\_NOADREG}$	Without ADREG.	655	565	468	453	423	MHz
$F_{MAX\_NOPIPELINEREG}$	Without pipeline registers (MREG, ADREG).	483	410	338	323	304	MHz
$F_{MAX\_NOPIPELINEREG\_PATDET}$	Without pipeline registers (MREG, ADREG) with pattern detect.	448	379	314	299	280	MHz

Clock Buffers and Networks

Table 84: **Clock Buffers Switching Characteristics**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
Global Clock Switching Characteristics (Including BUFGCTRL)							
F_{MAX}	Maximum frequency of a global clock tree (BUFG).	891	775	667	725	667	MHz
Global Clock Buffer with Input Divide Capability (BUFGCE_DIV)							
F_{MAX}	Maximum frequency of a global clock buffer with input divide capability (BUFGCE_DIV).	891	775	667	725	667	MHz
Global Clock Buffer with Clock Enable (BUFGCE)							
F_{MAX}	Maximum frequency of a global clock buffer with clock enable (BUFGCE).	891	775	667	725	667	MHz
Leaf Clock Buffer with Clock Enable (BUFCE_LEAF)							
F_{MAX}	Maximum frequency of a leaf clock buffer with clock enable (BUFCE_LEAF).	891	775	667	725	667	MHz
GTH or GTY Clock Buffer with Clock Enable and Clock Input Divide Capability (BUFG_GT)							
F_{MAX}	Maximum frequency of a serial transceiver clock buffer with clock enable and clock input divide capability.	512	512	512	512	512	MHz

MMCM Switching Characteristics

Table 85: **MMCM Specification**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
$MMCM\_F_{INMAX}$	Maximum input clock frequency.	1066	933	800	933	800	MHz
$MMCM\_F_{INMIN}$	Minimum input clock frequency.	10	10	10	10	10	MHz
$MMCM\_F_{INJITTER}$	Maximum input clock period jitter.	< 20% of clock input period or 1 ns Max					
$MMCM\_F_{INDUTY}$	Input duty cycle range: 10–49 MHz.	25–75					%
	Input duty cycle range: 50–199 MHz.	30–70					%
	Input duty cycle range: 200–399 MHz.	35–65					%
	Input duty cycle range: 400–499 MHz.	40–60					%
	Input duty cycle range: >500 MHz.	45–55					%
$MMCM\_F_{MIN\_PSCLK}$	Minimum dynamic phase shift clock frequency.	0.01	0.01	0.01	0.01	0.01	MHz
$MMCM\_F_{MAX\_PSCLK}$	Maximum dynamic phase shift clock frequency.	550	500	450	500	450	MHz
$MMCM\_F_{VCOMIN}$	Minimum MMCM VCO frequency.	800	800	800	800	800	MHz
$MMCM\_F_{VCOMAX}$	Maximum MMCM VCO frequency.	1600	1600	1600	1600	1600	MHz
$MMCM\_F_{BANDWIDTH}$	Low MMCM bandwidth at typical.(1)	1.00	1.00	1.00	1.00	1.00	MHz
	High MMCM bandwidth at typical.(1)	4.00	4.00	4.00	4.00	4.00	MHz
$MMCM\_T_{STATPHAOFFSET}$	Static phase offset of the MMCM outputs.(2)	0.12	0.12	0.12	0.12	0.12	ns
$MMCM\_T_{OUTJITTER}$	MMCM output jitter.	Note 3					
$MMCM\_T_{OUTDUTY}$	MMCM output clock duty cycle precision.(4)	0.165	0.20	0.20	0.20	0.20	ns
$MMCM\_T_{LOCKMAX}$	MMCM maximum lock time for $MMCM\_F_{PFDMIN}$.	100	100	100	100	100	µs
$MMCM\_F_{OUTMAX}$	MMCM maximum output frequency.	891	775	667	725	667	MHz
$MMCM\_F_{OUTMIN}$	MMCM minimum output frequency.(4)(5)	6.25	6.25	6.25	6.25	6.25	MHz
$MMCM\_T_{EXTFDVAR}$	External clock feedback variation.	< 20% of clock input period or 1 ns Max					
$MMCM\_RST_{MINPULSE}$	Minimum reset pulse width.	5.00	5.00	5.00	5.00	5.00	ns
$MMCM\_F_{PFDMAX}$	Maximum frequency at the phase frequency detector.	550	500	450	500	450	MHz
$MMCM\_F_{PFDMIN}$	Minimum frequency at the phase frequency detector.	10	10	10	10	10	MHz
$MMCM\_T_{FBDELAY}$	Maximum delay in the feedback path.	5 ns Max or one clock cycle					

Table 85: **MMCM Specification *(Cont'd)***

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
MMCM_F_{DPRCLK_MAX}	Maximum DRP clock frequency	250	250	250	250	250	MHz

Notes:

1. The MMCM does not filter typical spread-spectrum input clocks because they are usually far below the bandwidth filter frequencies.
2. The static offset is measured between any MMCM outputs with identical phase.
3. Values for this parameter are available in the Clocking Wizard.
4. Includes global clock buffer.
5. Calculated as F_{VCO}/128 assuming output duty cycle is 50%.

Table 91: **Global Clock Input Setup and Hold With MMCM**

Symbol	Description		Device	Speed Grade and V_{CCINT} Operating Voltages					Units
				0.90V	0.85V		0.72V		
				-3	-2	-1	-2	-1	
Input Setup and Hold Time Relative to Global Clock Input Signal using SSTL15 Standard.(1)(2)(3)									
$T_{PSMMCMCC\_ZU2}$	Global clock input and input flip-flop (or latch) with MMCM.	Setup	XCZU2	N/A	1.83	1.96	2.29	2.48	ns
$T_{PHMMCMCC\_ZU2}$		Hold			–0.19	–0.19	0.13	0.13	ns
$T_{PSMMCMCC\_ZU3}$		Setup	XCZU3	N/A	1.83	1.96	2.29	2.48	ns
$T_{PHMMCMCC\_ZU3}$		Hold			–0.19	–0.19	0.13	0.13	ns
$T_{PSMMCMCC\_ZU4}$		Setup	XCZU4	1.96	1.96	2.10	2.49	2.59	ns
$T_{PHMMCMCC\_ZU4}$		Hold		–0.12	–0.12	–0.12	0.27	0.48	ns
$T_{PSMMCMCC\_ZU5}$		Setup	XCZU5	1.96	1.96	2.10	2.49	2.59	ns
$T_{PHMMCMCC\_ZU5}$		Hold		–0.12	–0.12	–0.12	0.27	0.48	ns
$T_{PSMMCMCC\_ZU6}$		Setup	XCZU6	1.97	2.00	2.12	2.26	2.44	ns
$T_{PHMMCMCC\_ZU6}$		Hold		–0.11	–0.11	–0.11	0.16	0.18	ns
$T_{PSMMCMCC\_ZU7}$		Setup	XCZU7	1.91	1.91	2.02	2.45	2.70	ns
$T_{PHMMCMCC\_ZU7}$		Hold		–0.14	–0.14	–0.14	0.37	0.38	ns
$T_{PSMMCMCC\_ZU9}$		Setup	XCZU9	1.97	2.00	2.12	2.26	2.44	ns
$T_{PHMMCMCC\_ZU9}$		Hold		–0.11	–0.11	–0.11	0.16	0.18	ns
$T_{PSMMCMCC\_ZU11}$		Setup	XCZU11	2.08	2.08	2.23	2.59	2.75	ns
$T_{PHMMCMCC\_ZU11}$		Hold		–0.08	–0.08	0.04	0.35	0.74	ns
$T_{PSMMCMCC\_ZU15}$		Setup	XCZU15	1.96	1.99	2.12	2.26	2.44	ns
$T_{PHMMCMCC\_ZU15}$		Hold		–0.10	–0.10	–0.10	0.17	0.19	ns
$T_{PSMMCMCC\_ZU17}$		Setup	XCZU17	1.89	1.89	2.03	2.36	2.55	ns
$T_{PHMMCMCC\_ZU17}$		Hold		–0.16	–0.16	–0.16	0.31	0.34	ns
$T_{PSMMCMCC\_ZU19}$		Setup	XCZU19	1.89	1.89	2.03	2.36	2.55	ns
$T_{PHMMCMCC\_ZU19}$		Hold		–0.16	–0.16	–0.16	0.31	0.34	ns

Notes:

1. Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, slowest temperature, and slowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, fastest temperature, and fastest voltage.
2. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.
3. Use IBIS to determine any duty-cycle distortion incurred using various standards.

Table 92: **Sampling Window**

Description	Speed Grade and V_{CCINT} Operating Voltages					Units
	0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	
T_{SAMP_BUFG} (1)	510	610	610	610	610	ps
$T_{SAMP\_NATIVE\_DPA}$	100	100	125	125	150	ps
$T_{SAMP\_NATIVE\_BISC}$	60	60	85	85	110	ps

Notes:

1. This parameter indicates the total sampling error of the Zynq UltraScale+ MPSoC DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the MMCM to capture the DDR input registers' edges of operation. These measurements include: CLK0 MMCM jitter, MMCM accuracy (phase offset), and MMCM phase shift resolution. These measurements do not include package or clock tree skew.

GTH Transceiver Specifications

The *UltraScale Architecture and Product Overview* (DS890) lists the Zynq UltraScale+ MPSoCs that include the GTH transceivers.

GTH Transceiver DC Input and Output Levels

Table 94 summarizes the DC specifications of the GTH transceivers in Zynq UltraScale+ MPSoC. Consult the *UltraScale Architecture GTH Transceiver User Guide* (UG576) for further details.

Table 94: **GTH Transceiver DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
DV_{PPIN}	Differential peak-to-peak input voltage (external AC coupled).	>10.3125 Gb/s	150	–	1250	mV
		6.6 Gb/s to 10.3125 Gb/s	150	–	1250	mV
		≤ 6.6 Gb/s	150	–	2000	mV
V_{IN}	Single-ended input voltage. Voltage measured at the pin referenced to GND.	DC coupled $V_{MGTAVTT}$ = 1.2V	–400	–	$V_{MGTAVTT}$	mV
V_{CMIN}	Common mode input voltage.	DC coupled $V_{MGTAVTT}$ = 1.2V	–	2/3 $V_{MGTAVTT}$	–	mV
D_{VPPOUT}	Differential peak-to-peak output voltage.(1)	Transmitter output swing is set to 11111	800	–	–	mV
$V_{CMOUTDC}$	Common mode output voltage: DC coupled (equation based).	When remote RX is terminated to GND	$V_{MGTAVTT}/2 - D_{VPPOUT}/4$			mV
		When remote RX termination is floating	$V_{MGTAVTT} - D_{VPPOUT}/2$			mV
		When remote RX is terminated to V_{RX_TERM}(2)	$V_{MGTAVTT} - \frac{D_{VPPOUT}}{4} - \left(\frac{V_{MGTAVTT} - V_{RX\_TERM}}{2}\right)$			mV
$V_{CMOUTAC}$	Common mode output voltage: AC coupled (equation based).		$V_{MGTAVTT} - D_{VPPOUT}/2$			mV
R_{IN}	Differential input resistance.		–	100	–	Ω
R_{OUT}	Differential output resistance.		–	100	–	Ω
T_{OSKEW}	Transmitter output pair (TXP and TXN) intra-pair skew (all packages).		–	–	10	ps
C_{EXT}	Recommended external AC coupling capacitor.(3)		–	100	–	nF

Notes:

1. The output swing and pre-emphasis levels are programmable using the attributes discussed in the *UltraScale Architecture GTH Transceiver User Guide* (UG576), and can result in values lower than reported in this table.
2. V_{RX_TERM} is the remote RX termination voltage.
3. Other values can be used as appropriate to conform to specific protocols and standards.

Table 103: **GTH Transceiver Transmitter Switching Characteristics *(Cont'd)***

Symbol	Description	Condition	Min	Typ	Max	Units
$T_{J2.5}$	Total jitter(3)(4)	2.5 Gb/s(6)	–	–	0.20	UI
$D_{J2.5}$	Deterministic jitter(3)(4)		–	–	0.10	UI
$T_{J1.25}$	Total jitter(3)(4)	1.25 Gb/s(7)	–	–	0.15	UI
$D_{J1.25}$	Deterministic jitter(3)(4)		–	–	0.06	UI
T_{J500}	Total jitter(3)(4)	500 Mb/s(8)	–	–	0.10	UI
D_{J500}	Deterministic jitter(3)(4)		–	–	0.03	UI

Notes:

1. Using same REFCLK input with TX phase alignment enabled for up to four consecutive transmitters (one fully populated GTH Quad) at the maximum line rate.
2. Using QPLL_FBDIV = 40, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
3. Using CPLL_FBDIV = 2, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
4. All jitter values are based on a bit-error ratio of 10^{-12}.
5. CPLL frequency at 3.2 GHz and TXOUT_DIV = 2.
6. CPLL frequency at 2.5 GHz and TXOUT_DIV = 2.
7. CPLL frequency at 2.5 GHz and TXOUT_DIV = 4.
8. CPLL frequency at 2.0 GHz and TXOUT_DIV = 8.

Table 104: **GTH Transceiver Receiver Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTHRX}	Serial data rate		0.500	–	F_{GTHMAX}	Gb/s
R_{XSST}	Receiver spread-spectrum tracking(1)	Modulated at 33 kHz	–5000	–	0	ppm
R_{XRL}	Run length (CID)		–	–	256	UI
$R_{XPPMTOL}$	Data/REFCLK PPM offset tolerance	Bit rates ≤ 6.6 Gb/s	–1250	–	1250	ppm
		Bit rates > 6.6 Gb/s and ≤ 8.0 Gb/s	–700	–	700	ppm
		Bit rates > 8.0 Gb/s	–200	–	200	ppm
SJ Jitter Tolerance(2)						
$J_{T\_SJ16.375}$	Sinusoidal jitter (QPLL)(3)	16.375 Gb/s	0.30	–	–	UI
$J_{T\_SJ15.0}$	Sinusoidal jitter (QPLL)(3)	15.0 Gb/s	0.30	–	–	UI
$J_{T\_SJ14.1}$	Sinusoidal jitter (QPLL)(3)	14.1 Gb/s	0.30	–	–	UI
$J_{T\_SJ13.1}$	Sinusoidal jitter (QPLL)(3)	13.1 Gb/s	0.30	–	–	UI
$J_{T\_SJ12.5}$	Sinusoidal jitter (QPLL)(3)	12.5 Gb/s	0.30	–	–	UI
$J_{T\_SJ11.3}$	Sinusoidal jitter (QPLL)(3)	11.3 Gb/s	0.30	–	–	UI
$J_{T\_SJ10.32\_QPLL}$	Sinusoidal jitter (QPLL)(3)	10.32 Gb/s	0.30	–	–	UI
$J_{T\_SJ10.32\_CPLL}$	Sinusoidal jitter (CPLL)(3)	10.32 Gb/s	0.30	–	–	UI
$J_{T\_SJ9.953\_QPLL}$	Sinusoidal jitter (QPLL)(3)	9.953 Gb/s	0.30	–	–	UI
$J_{T\_SJ9.953\_CPLL}$	Sinusoidal jitter (CPLL)(3)	9.953 Gb/s	0.30	–	–	UI
$J_{T\_SJ8.0}$	Sinusoidal jitter (QPLL)(3)	8.0 Gb/s	0.42	–	–	UI
$J_{T\_SJ6.6\_CPLL}$	Sinusoidal jitter (CPLL)(3)	6.6 Gb/s	0.44	–	–	UI
$J_{T\_SJ5.0}$	Sinusoidal jitter (CPLL)(3)	5.0 Gb/s	0.44	–	–	UI
$J_{T\_SJ4.25}$	Sinusoidal jitter (CPLL)(3)	4.25 Gb/s	0.44	–	–	UI
$J_{T\_SJ3.2}$	Sinusoidal jitter (CPLL)(3)	3.2 Gb/s(4)	0.45	–	–	UI

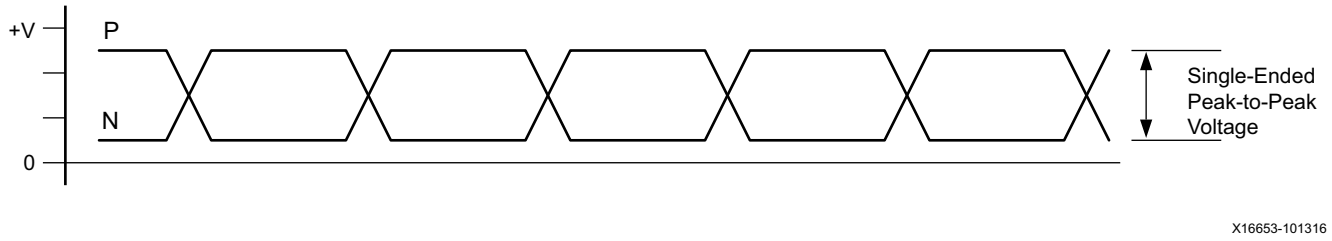

Figure 5: **Single-Ended Peak-to-Peak Voltage**

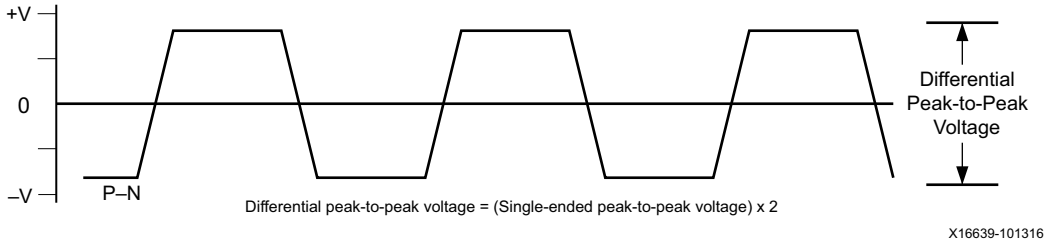

Figure 6: **Differential Peak-to-Peak Voltage**

Table 107 and Table 108 summarize the DC specifications of the clock input of the GTY transceivers in Zynq UltraScale+ MPSoCs. Consult the *UltraScale Architecture GTY Transceiver User Guide* (UG578) for further details.

Table 107: **GTY Transceiver Clock DC Input Level Specification**

Symbol	DC Parameter	Min	Typ	Max	Units
V_{IDIFF}	Differential peak-to-peak input voltage	250	–	2000	mV
R_{IN}	Differential input resistance	–	100	–	Ω
C_{EXT}	Required external AC coupling capacitor	–	10	–	nF

Table 108: **GTY Transceiver Clock Output Level Specification**

Symbol	Description	Conditions	Min	Typ	Max	Units
V_{OL}	Output Low voltage for P and N	R_T = 100Ω across P and N signals	100	–	330	mV
V_{OH}	Output High voltage for P and N	R_T = 100Ω across P and N signals	500	–	700	mV
V_{DDOUT}	Differential output voltage (P–N), P = High (N–P), N = High	R_T = 100Ω across P and N signals	300	–	430	mV
V_{CMOUT}	Common mode voltage	R_T = 100Ω across P and N signals	300	–	500	mV

GTY Transceiver Electrical Compliance

The *UltraScale Architecture GTY Transceiver User Guide* (UG578) contains recommended use modes that ensure compliance for the protocols listed in Table 117. The transceiver wizard provides the recommended settings for those use cases and for protocol specific characteristics.

Table 117: **GTY Transceiver Protocol List**

Protocol	Specification	Serial Rate (Gb/s)	Electrical Compliance
CAUI-4	IEEE 802.3-2012	25.78125	Compliant
28 Gb/s backplane	CEI-25G-LR	25–28.05	Compliant
Interlaken	OIF-CEI-6G, OIF-CEI-11GSR, OIF-CEI-28G-MR	4.25–25.78125	Compliant
100GBASE-KR4	IEEE 802.3bj-2014, CEI-25G-LR	25.78125	Compliant(1)
100GBASE-CR4	IEEE 802.3bj-2014, CEI-25G-LR	25.78125	Compliant(1)
50GBASE-KR4	IEEE 802.3by-2014, CEI-25G-LR	25.78125	Compliant(1)
50GBASE-CR4	IEEE 802.3by-2014, CEI-25G-LR	25.78125	Compliant(1)
25GBASE-KR4	IEEE 802.3by-2014, CEI-25G-LR	25.78125	Compliant(1)
25GBASE-CR4	IEEE 802.3by-2014, CEI-25G-LR	25.78125	Compliant(1)
OTU4 (OTL4.4) CFP2	OIF-CEI-28G-VSR	27.952493–32.75	Compliant
OTU4 (OTL4.4) CFP	OIF-CEI-11G-MR	11.18–13.1	Compliant
CAUI-10	IEEE 802.3-2012	10.3125	Compliant
nPPI	IEEE 802.3-2012	10.3125	Compliant
10GBASE-KR(2)	IEEE 802.3-2012	10.3125	Compliant
SFP+	SFF-8431 (SR and LR)	9.95328–11.10	Compliant
XFP	INF-8077i, revision 4.5	10.3125	Compliant
RXAUI	CEI-6G-SR	6.25	Compliant
XAUI	IEEE 802.3-2012	3.125	Compliant
1000BASE-X	IEEE 802.3-2012	1.25	Compliant
5.0G Ethernet	IEEE 802.3bx (PAR)	5	Compliant
2.5G Ethernet	IEEE 802.3bx (PAR)	2.5	Compliant
HiGig, HiGig+, HiGig2	IEEE 802.3-2012	3.74, 6.6	Compliant
QSGMII	QSGMII v1.2 (Cisco System, ENG-46158)	5	Compliant
OTU2	ITU G.8251	10.709225	Compliant
OTU4 (OTL4.10)	OIF-CEI-11G-SR	11.180997	Compliant
OC-3/12/48/192	GR-253-CORE	0.1555–9.956	Compliant
PCIe Gen1, 2, 3	PCI Express base 3.0	2.5, 5.0, and 8.0	Compliant
SDI(3)	SMPTE 424M-2006	0.27–2.97	Compliant
UHD-SDI(3)	SMPTE ST-2081 6G, SMPTE ST-2082 12G	6 and 12	Compliant
Hybrid memory cube (HMC)	HMC-15G-SR	10, 12.5, and 15.0	Compliant
MoSys bandwidth engine	CEI-11-SR and CEI-11-SR (overclocked)	10.3125, 15.5	Compliant
CPRI	CPRI_v_6_1_2014-07-01	0.6144–12.165	Compliant
Passive optical network (PON)	10G-EPON, 1G-EPON, NG-PON2, XG-PON, and 2.5G-PON	0.155–10.3125	Compliant
JESD204a/b	OIF-CEI-6G, OIF-CEI-11G	3.125–12.5	Compliant

PL SYSMON I2C/PMBus Interfaces

Table 125: **PL SYSMON I2C Fast Mode Interface Switching Characteristics(1)**

Symbol	Description	Min	Max	Units
T_{SMFCKL}	SCL Low time	1.3	–	µs
T_{SMFCKH}	SCL High time	0.6	–	µs
T_{SMFCKO}	SDAO clock-to-out delay	–	900	ns
T_{SMFDCK}	SDAI setup time	100	–	ns
F_{SMFCLK}	SCL clock frequency	–	400	kHz

Notes:
1. The test conditions are configured to the LVCMOS 1.8V I/O standard.

Table 126: **PL SYSMON I2C Standard Mode Interface Switching Characteristics(1)**

Symbol	Description	Min	Max	Units
T_{SMSCKL}	SCL Low time	4.7	–	µs
T_{SMSCKH}	SCL High time	4.0	–	µs
T_{SMSCKO}	SDAO clock-to-out delay	–	3450	ns
T_{SMSDCK}	SDAI setup time	250	–	ns
F_{SMSCLK}	SCL clock frequency	–	100	kHz

Notes:
1. The test conditions are configured to the LVCMOS 1.8V I/O standard.

Revision History

The following table shows the revision history for this document.

Date	Version	Description of Revisions
04/20/2017	1.3	Updated Table 25, Table 26, and Table 27 to production release for the following devices/speed/temperature grades in Vivado Design Suite 2017.1. XCZU2CG and XCZU2EG: –2E, -2I, -1E, -1I XCZU3CG and XCZU3EG: –2E, -2I, -1E, -1I XCZU6CG and XCZU6EG: –2E, -2I, -1E, -1I XCZU9CG and XCZU9EG: –2E, -2I, -1E, -1I Added -2E (V_{CCINT} = 0.85V) speed grade where applicable. Removed -3E speed grade from the XCZU2 and XCZU3 devices in Table 26 and where applicable. In Table 1, updated values and Note 2. In Table 2, added or updated many of the notes. Updated Table 4 including the notes and added Note 6. Moved and updated Table 5. Added Table 8. Updated Table 9 and added Note 4. Updated Table 10 and added Note 1. Revised V_{ICM} in Table 23. Updated Table 30 and removed Note 1. Added Table 31 and Table 32. Updated Table 33 and removed F_{FTMCLK}. Updated $T_{RFPSCLK}$ in Table 34. Updated Note 1 in Table 37. Updated Table 39. Removed the *PS NAND Memory Controller Interface* section. Significant changes to Table 41 and removed Note 3. Significant changes to Table 42 and updated Note 1. Removed $F_{TSU\_REF\_CLK}$ from Table 44. Revised Table 45 and added Note 2 and Note 3. Revised Table 46 and added Note 2 and Note 3. Updated Table 48. Updated Table 51 and removed Note 2. Revised Table 52. Revised many of the tables in the PS-GTR Transceiver section. Revised Table 70 and Table 71. Removed Note 8 from Table 74. Updated the values in Table 75, Table 76, Table 77, Table 80, Table 87, Table 88, Table 89, Table 90,and Table 91 to the Vivado Design Suite 2017.1 speed specifications. Updated the values in Table 81 and Table 82. Added values to Table 92. Updated Table 93. Revised D_{VPPOUT} in Table 94. Update the values in Table 96. Added Note 6 to Table 102. Updated Table 103 and Table 104. Revised D_{VPPOUT} in Table 106. Updated the values in Table 108. In Table 109 updated the -1 (0.85V) specifications and removed Note 1. In Table 114 updated the -1 (0.85V) specifications and added Note 6. In Table 115 and Table 116, added the 28.21 jitter tolerance values and revised the notes. Revised the Integrated Interface Block for Interlaken and Integrated Interface Block for 100G Ethernet MAC and PCS sections. Revised the Configuration Switching Characteristics section. Removed the *eFUSE Programming Conditions* table and added the specifications to Table 2 and Table 3.

Date	Version	Description of Revisions
02/10/2017	1.2	Updated some of the maximum voltages in the Processor System (PS) section and other specifications in the Programmable Logic (PL) and GTH or GTY Transceiver sections of Table 1. Updated Table 2, Table 4, Table 6, Table 7, and Table 9. Revised the Power Supply Sequencing section including Table 10. Added PS and VCU ramp times to Table 11. Revised V_{ODIFF} in Table 24. Updated Table 25. Added Note 1 to Table 26. Table 30 replaces the previous three PS memory performance tables. Added values to Table 34, Table 37, and Table 38. Deleted the waveforms in the PS Switching Characteristics section (Figures 1-16 and Figures 25-26). Revised values in the *PS NAND Memory Controller Interface* section. Added and updated data in Table 40. Added Note 3 to Table 41. Added Note 3 to Table 42. Added Note 1 to Table 45. Updated Table 48 and removed Note 3. Added data to Table 56. Updated Table 60. Added Table 61. Updated Table 63. Revised Table 69. Added data to Table 70. Added Note 2 to Table 71. Updated Table 74 and added Note 4. Updated V_L and V_H values in Table 78. Added T_{MINPER_CLK}, revised F_{REFCLK}, and Note 1 to Table 82. Added MMCM_F_{DPRCLK_MAX} to Table 85 and PLL_F_{DPRCLK_MAX} to Table 86. Added data to Table 94, Table 96, Table 98, Table 101, and updated the note references in Table 102. Updated Table 103 and added Note 8. Updated Table 104 and added Note 7. Added more protocols, Note 1 and Note 2 to Table 105. Removed the *GTH Transceiver Protocol Jitter Characteristics* section because it is covered in Table 105. Added Note 1 to Table 109. Added data to Table 106, Table 108, Table 110, Table 113. Added Note 2 to Table 112. Added note references in Table 114. Updated Table 115 and added Note 8. Updated Table 116 and added Note 7. Added more protocols and Note 3 to Table 117. Removed the *GTY Transceiver Protocol Jitter Characteristics* section because it is covered in Table 117. Revised Table 124. Added T_{POR} and updated F_{ICAPCK} in Table 127. Updated the Automotive Applications Disclaimer.
06/20/2016	1.1	Updated the Summary description. In Table 1, revised V_{IN} for HP I/O banks and added clarifications to some descriptions and symbols. Added I_{RPU}, I_{RPD}, and Note 4 to Table 2 and updated $V_{PS\_MGTRAVCC}$, the PL System Monitor section, and Note 3 and Note 5. Updated Note 5 in Table 4. Updated the PS Power-On/Off Power Supply Sequencing section including all the voltage supply names. Added MIPI_DPHY_DCI to Table 14, Table 15, and Table 17. Updated Table 23, including removing the V_{CCO} specification and adding Note 1. Added Note 1 to Table 24. Updated Table 25 speed specifications for Vivado Design Suite 2016.1. Added values to Table 28. Updated the -2 value in Table 29. Added $F_{DPLIVEVIDEO}$ and updated $F_{FCIDMACLK}$ in Table 33. Added VCO frequencies to Table 36. Added the T_{PSPOR} minimum to Table 37 and updated Note 1. Added Table 38. Added value delineation over V_{CCINT} operating voltages in Table 39. Revised values for F_{TCK} and T_{TAPTCK}/T_{TCKTAP} in Table 40 and added value delineation over V_{CCINT} operating voltages. Updated the *PS NAND Memory Controller Interface* section. Revised some units and Note 1 in Table 41 and Table 42. Removed Figure 6: Quad-SPI Interface (Feedback Clock Disabled) Timing. Updated Note 1 of Table 43. Added $F_{TSI\_REF\_CLK}$ to Table 44 and updated Note 1. In Table 45, revised $T_{DCSDHSCLK1}$, $T_{DCSDHSCLK2}$, and $T_{DCSDHSCLK3}$ and Note 1. In Table 46, revised Note 1. In Table 47, revised Note 1. Revised Table 48, including Note 1, and added Note 2 and Note 3. In Table 49, Table 50, Table 51, and Table 53, revised Note 1. Updated Table 71. Replaced Table 74. Updated Table 75 and Table 76. Updated Table 78 and Table 79. In Table 80, added the Block RAM and FIFO Clock-to-Out Delays section. Updated the R_{IN} and C_{EXT} values in Table 57 and Table 95. Updated the -2 (0.72V) and -1 (0.72V) values and added Note 1 to Table 97. Added Table 100 and Table 112. Added Note 2 to Table 106. Revised data in Table 109. Revised Table 114. Revised data and added notes in the Integrated Interface Block for Interlaken section and Table 121. Moved Table 123. Revised INL in Table 124. Added notes to Table 125 and Table 126. In the *eFUSE and Programming Conditions* table, updated the I_{PSFS} description.
11/24/2015	1.0	Initial Xilinx release.